

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1629	(257/335,339,340,343).CCLS	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2004/12/15 17:03
L2	498	1 and (trench or recess or sinker or groove)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2004/12/15 17:57
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L4	188	3 and ((Lateral adj dmos) or Idmos or dmos)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2004/12/15 17:11
L5	3	("4796070" "5349224" "5569949").PN. OR ("6548863").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/15 17:26
L6	24	("5445978" "5672526").PN. OR ("5918137").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/15 17:35
L7	14	("5539238").URPN.	USPAT	OR	OFF	2004/12/15 17:57
L8	719	(lateral adj dmos) or Idmos	USPAT	OR	OFF	2004/12/15 17:57
L9	719	8 and (@ad<"20031017" or @rlad<"20031017")	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2004/12/15 17:57
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L11	193	10 not 4	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2004/12/15 17:58
L12	3	("4796070" "5349224" "5569949").PN. OR ("6548863").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/15 18:44

L13	20	("20020130358" "20020177277" "4605948" "4754310" "5233215" "5323040" "5436173" "5449946" "5539238" "5592005" "5679966" "5710455" "5801431" "5844275" "5861657" "5874767" "5885878" "6040600" "6069396" "6307246").PN. OR ("6787872").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/15 18:45
L14	12	("4971926" "4980306" "4985368" "5242841" "5258332" "5539238" "5569949").PN. OR ("5696010"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/15 18:46



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16 An intelligent vertical trench DMOS on SIMOX-substrate

Vogt, F.; Vogt, H.; Brucker, J.; Zimmermann, C.; Richter, F.;
Power Semiconductor Devices and ICs, 1996. ISPSD '96 Proceedings., 8th
International Symposium on , 20-23 May 1996
Pages:177 - 180

[\[Abstract\]](#) [\[PDF Full-Text \(528 KB\)\]](#) IEEE CNF

17 A high reliability and low loss 3-phase gate driver IC with a novel soft gate drive circuit for 42V motor generator system

Inaba, M.; Sakano, J.; Miyazaki, H.; Iwamura, M.; Maeda, Y.; Mashino, K.; Nagai, Y.; Mori, M.;
Power Semiconductor Devices and ICs, 2003. Proceedings. ISPSD '03. 2003 IEEE
15th International Symposium on , 14-17 April 2003
Pages:97 - 100

[\[Abstract\]](#) [\[PDF Full-Text \(374 KB\)\]](#) IEEE CNF

18 Robust 80 V LDMOS and 100 V DECMOS in a streamlined SOI technology for analog power applications

Merchant, S.; Efland, T.; Haynie, S.; Headen, W.; Kajiyama, K.; Paiva, S.; Shaw, R.; Tachikake, I.; Tani, T.; Chin-Yu Tsai;
Power Semiconductor Devices and ICs, 2002. Proceedings of the 14th International
Symposium on , 4-7 June 2002
Pages:185 - 188

[\[Abstract\]](#) [\[PDF Full-Text \(426 KB\)\]](#) IEEE CNF

19 Trenched sinker LDMOSFET (TS-LDMOS) structure for high power amplifier application above 2 GHz

Cheon Soo Kim; Joung-Woo Park; Hyun Kyu Yu;
Electron Devices Meeting, 2001. IEDM Technical Digest. International , 2-5 Dec.